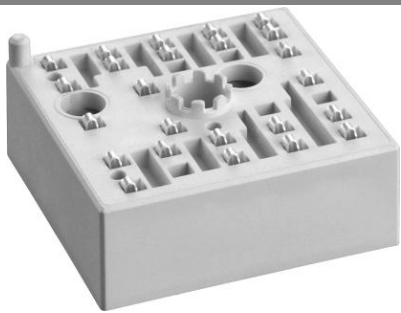


SKiiP 12NAB12T4V1



MiniSKiiP® 1

3-phase bridge rectifier +
brake chopper + 3-phase
bridge inverter
SKiiP 12NAB12T4V1

Features

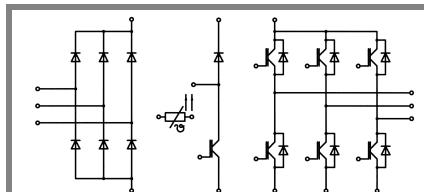
- Trench 4 IGBT's
- Robust and soft freewheeling diodes in CAL technology
- Highly reliable spring contacts for electrical connections
- UL recognised file no. E63532

Typical Applications*

- Inverter up to 12 kVA
- Typical motor power 5,5 kW

Remarks

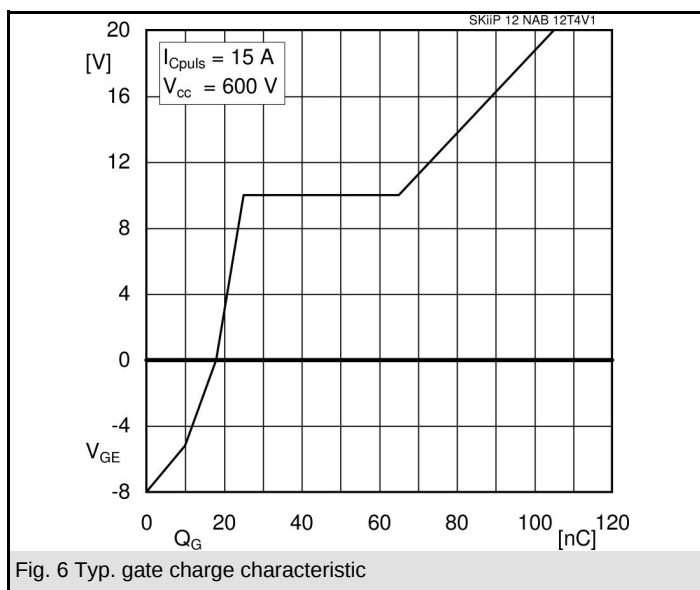
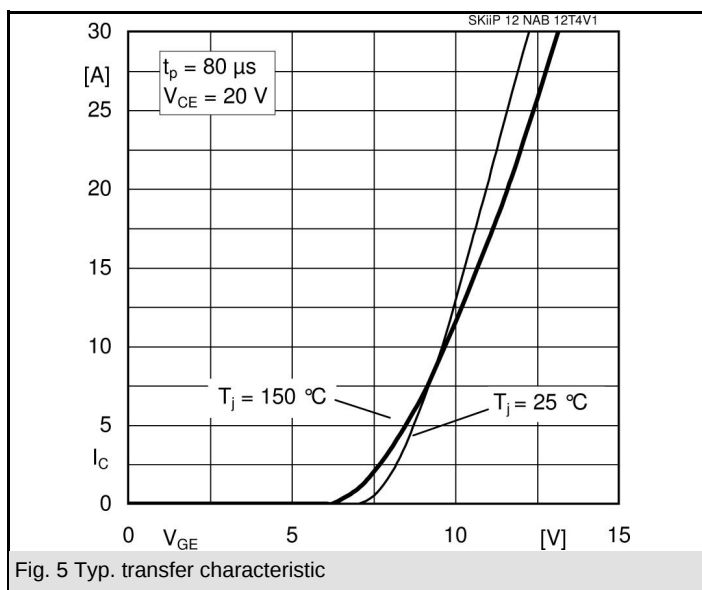
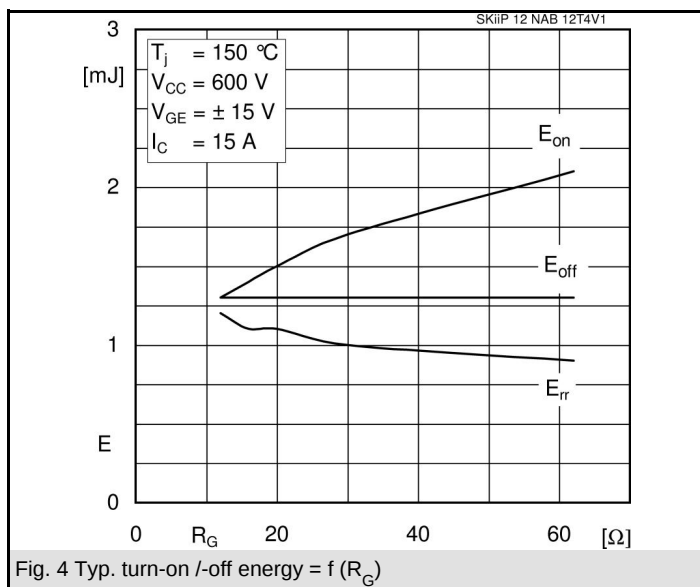
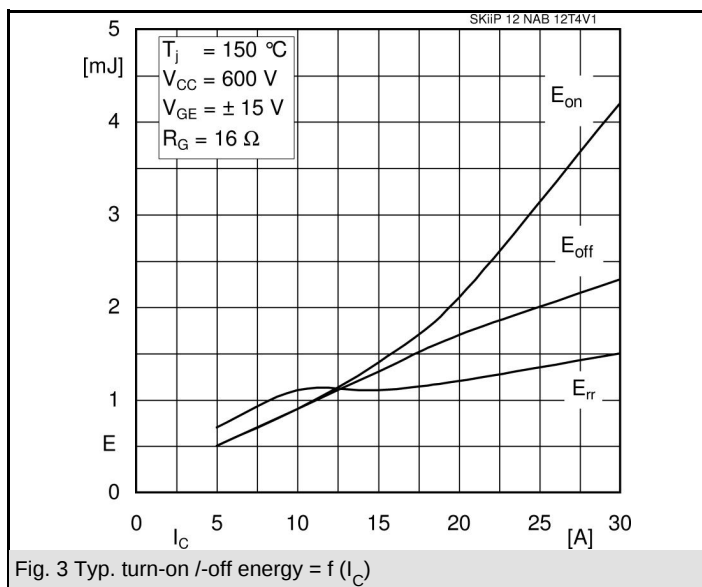
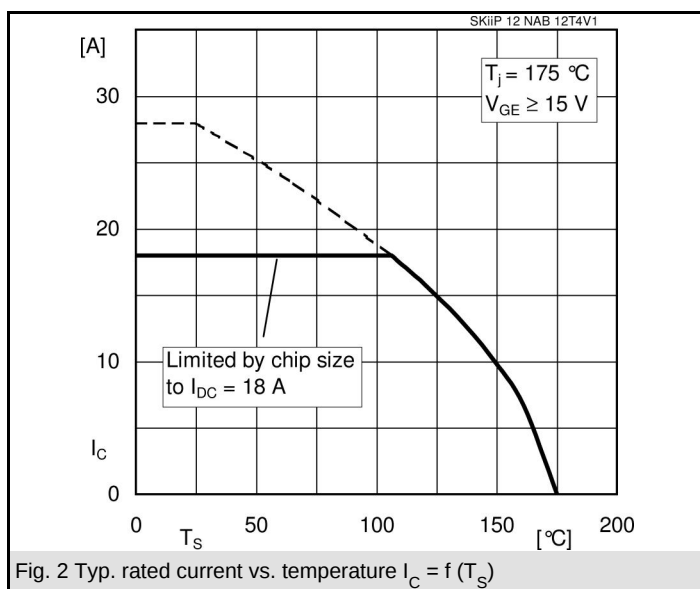
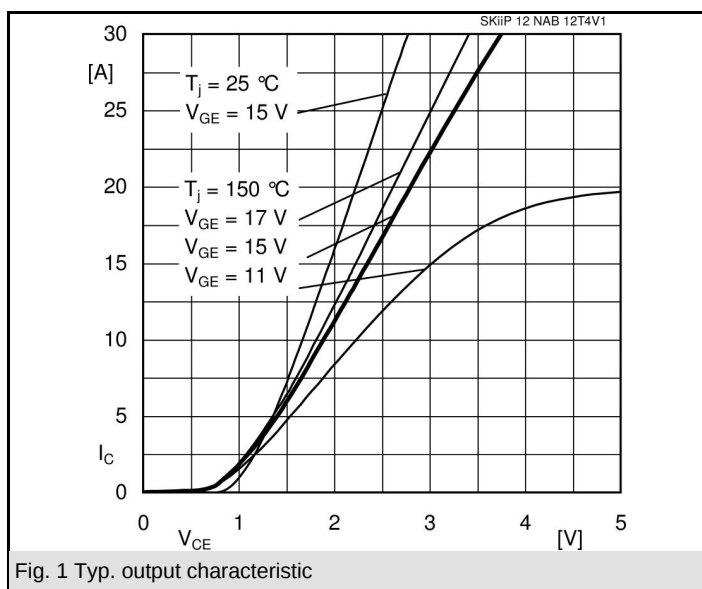
- V_{CEsat} , V_F = chip level value
- Case temp. limited to $T_C = 125^\circ\text{C}$ max. (for baseplateless modules $T_C = T_S$)
- product rel. results valid for $T_{j \leq 150}$ (recomm. $T_{op} = -40 \dots +150^\circ\text{C}$)

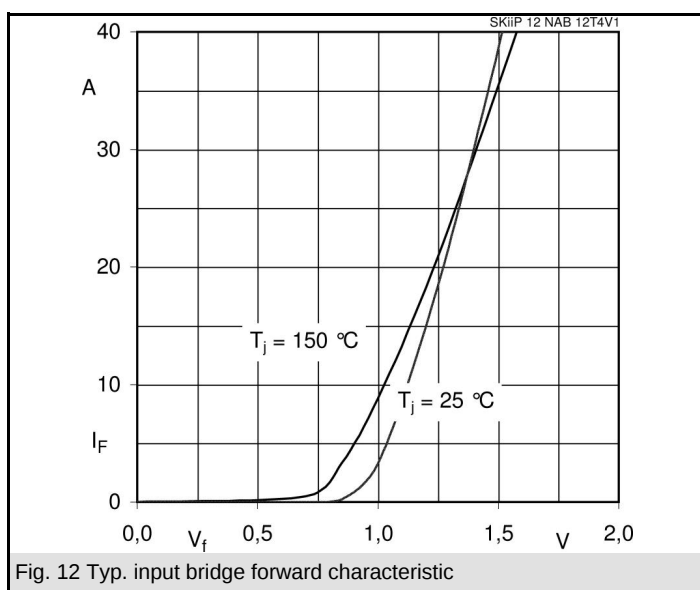
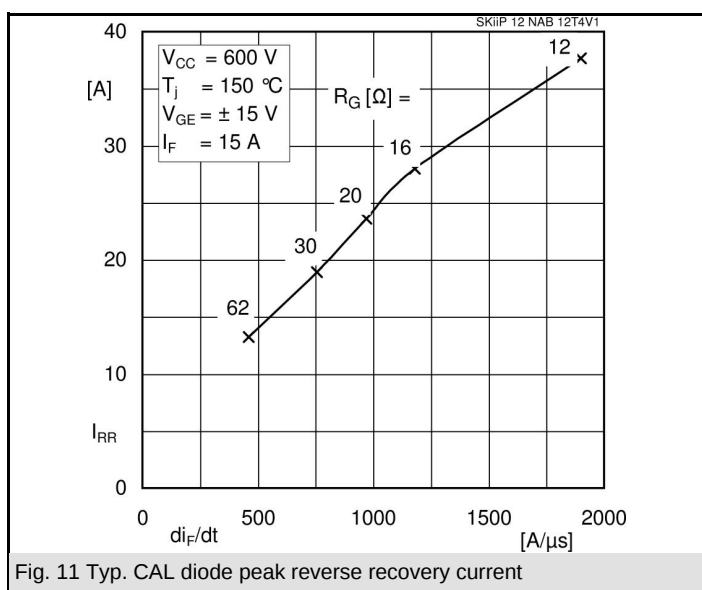
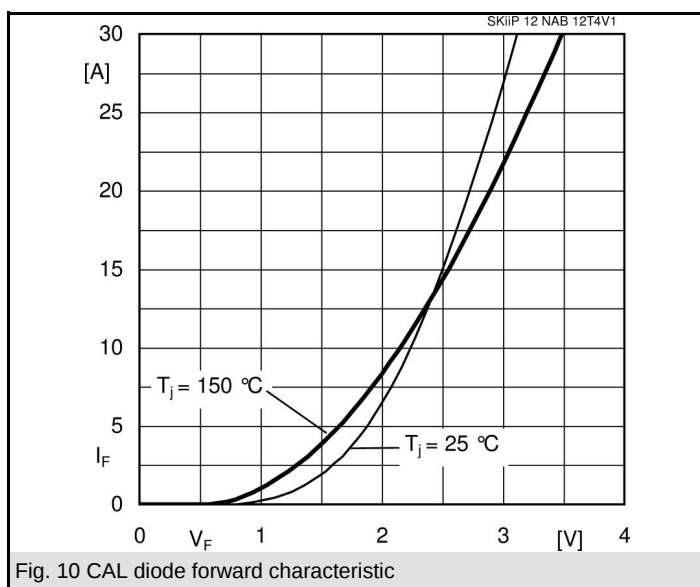
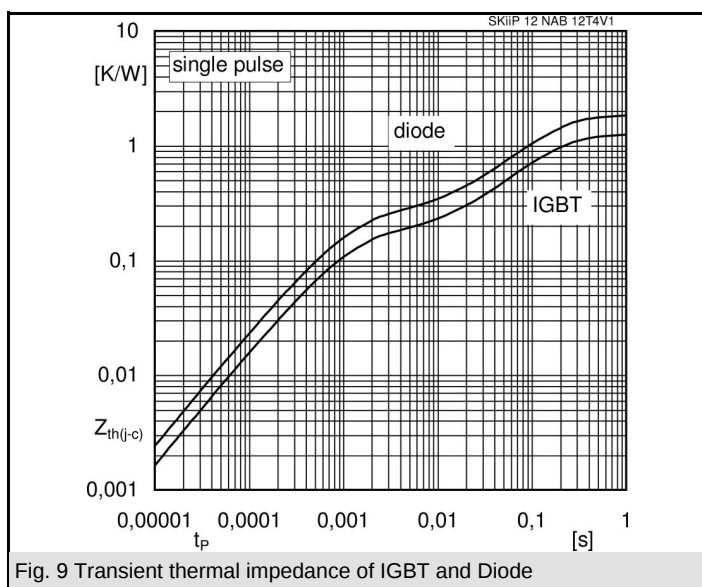
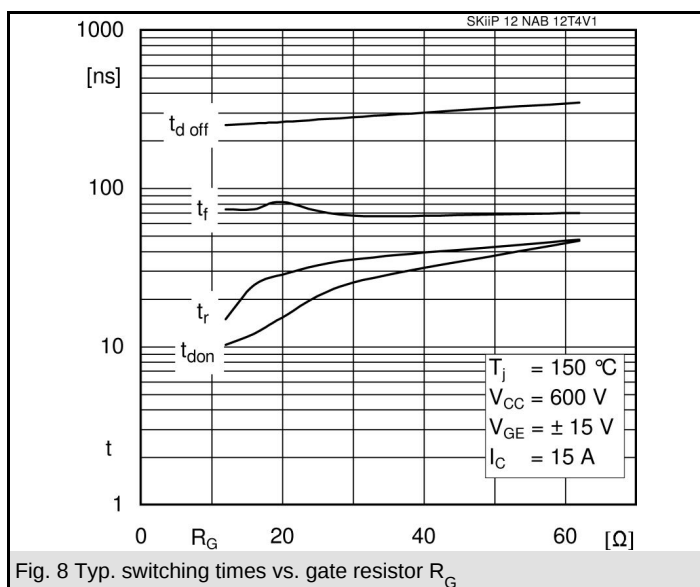
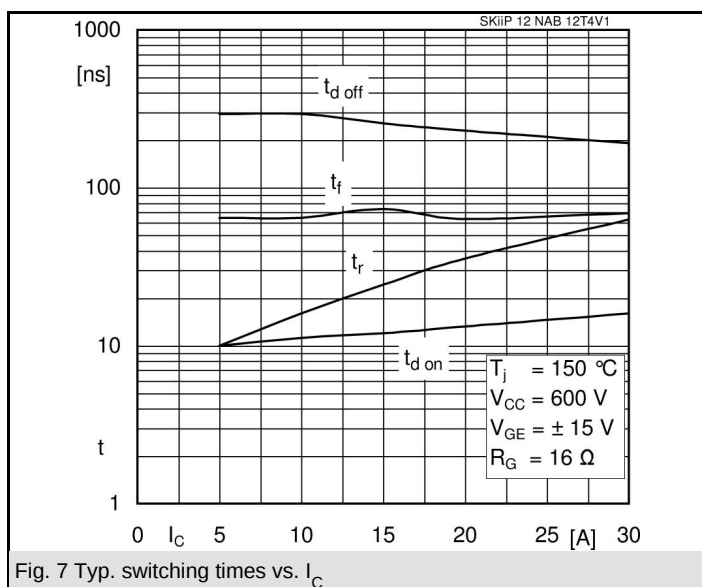


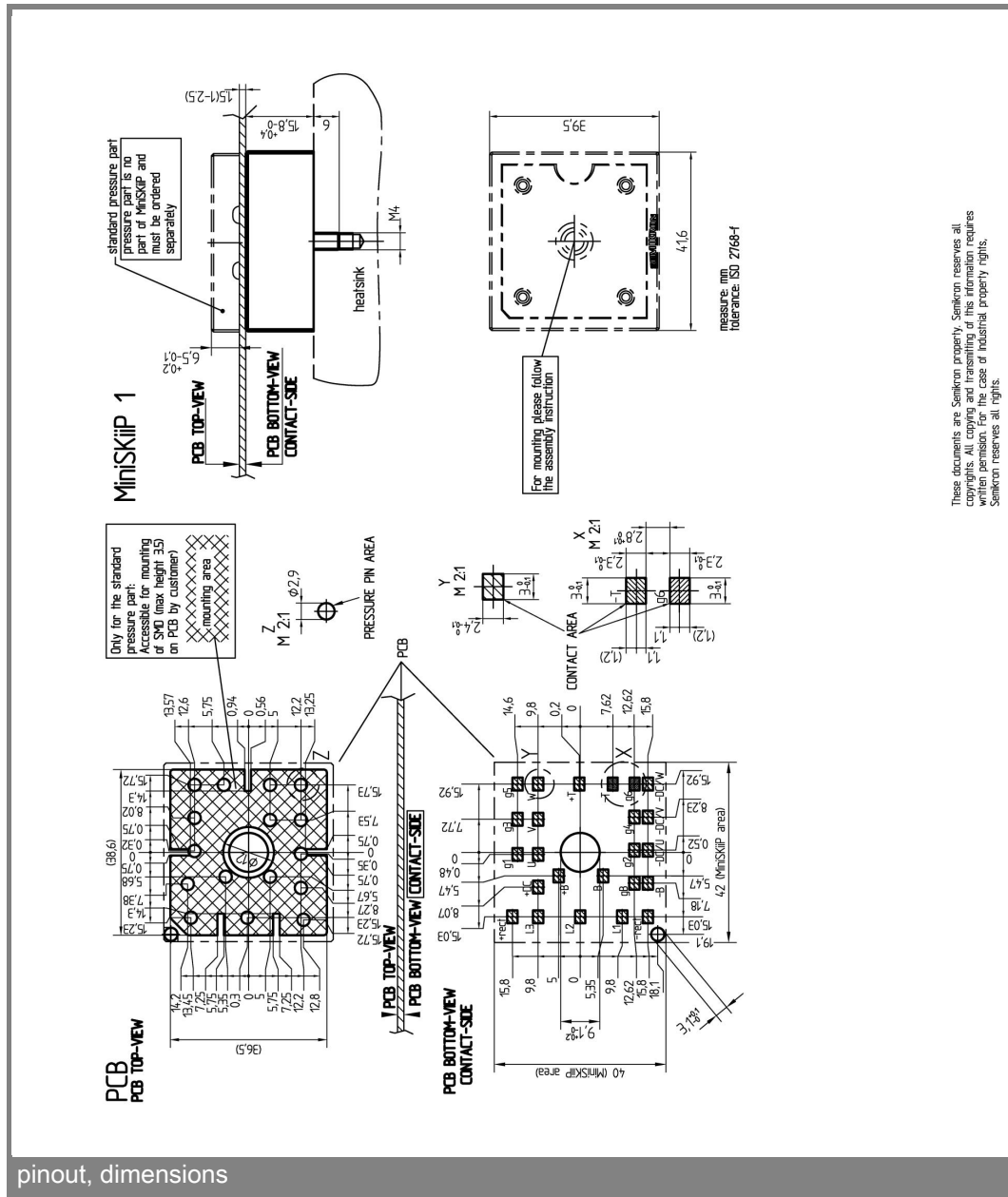
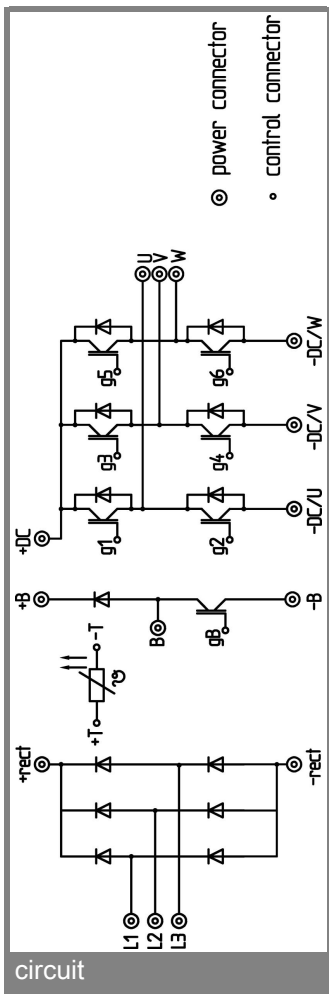
NAB

Absolute Maximum Ratings		T _s = 25 °C, unless otherwise specified		
Symbol	Conditions	Values	Units	
IGBT - Inverter, Chopper				
V _{CES}	T _s = 25 (70) °C	1200	V	
I _C		18 (18)	A	
I _{CRM}		45	A	
V _{GES}		± 20	V	
T _j		- 40 ... + 175	°C	
Diode - Inverter, Chopper				
I _F	T _s = 25 (70) °C	23 (18)	A	
I _{FRM}		45	A	
T _j		- 40 ... + 175	°C	
Diode - Rectifier				
V _{RRM}	T _s = 70 °C	1600	V	
I _F		35	A	
I _{FSM}		t _p = 10 ms, sin 180 °, T _j = 25 °C	220	A
i ² t		t _p = 10 ms, sin 180 °, T _j = 25 °C	240	A²s
T _j		- 40 ... + 150	°C	
Module				
I _{tRMS}	per power terminal (20 A / spring)	20	A	
T _{stg}		- 40 ... + 125	°C	
V _{isol}	AC, 1 min.	2500	V	

Characteristics		T _s = 25 °C, unless otherwise specified			
Symbol	Conditions	min.	typ.	max.	Units
IGBT - Inverter, Chopper					
V _{CEsat}	I _{Cnom} = 15 A, T _j = 25 (150) °C	5	1,85 (2,25)	2,1 (2,5)	V
V _{GE(th)}	V _{GE} = V _{CE} , I _C = 1 mA		5,8	6,5	V
V _{CE(TO)}	T _j = 25 (150) °C		0,8 (0,7)	0,9 (0,8)	V
r _T	T _j = 25 (150) °C		70 (103)	80 (113)	mΩ
C _{ies}	V _{CE} = 25 V, V _{GE} = 0 V, f = 1 MHz		0,9		nF
C _{oes}	V _{CE} = 25 V, V _{GE} = 0 V, f = 1 MHz		0,08		nF
C _{res}	V _{CE} = 25 V, V _{GE} = 0 V, f = 1 MHz		0,055		nF
R _{th(j-s)}	per IGBT		1,3		K/W
t _{d(on)}	under following conditions		15		ns
t _r	V _{CC} = 600 V, V _{GE} = ± 15 V		25		ns
t _{d(off)}	I _{Cnom} = 15 A, T _j = 150°C		260		ns
t _f	R _{Gon} = R _{Goff} = 16 Ω		75		ns
E _{on}	inductive load		1,4		mJ
E _{off}			1,3		mJ
Diode - Inverter, Chopper					
V _F = V _{EC}	I _{Fnom} = 15 A, T _j = 25 (150) °C		2,4 (2,45)	2,75 (2,8)	V
V _(TO)	T _j = 25 (150) °C		1,3 (0,9)	1,5 (1,1)	V
r _T	T _j = 25 (150) °C		73 (103)	83 (113)	mΩ
R _{th(j-s)}	per diode		1,92		K/W
I _{RRM}	under following conditions		28		A
Q _{rr}	I _{Fnom} = 15 A, V _R = 600 V		2,6		μC
E _{rr}	V _{GE} = 0 V, T _j = 150 °C		1,1		mJ
	di _F /dt = 1180 A/μs				
Diode - Rectifier					
V _F	I _{Fnom} = 15 A, T _j = 25 °C		1,1		V
V _(TO)	T _j = 150 °C		0,8		V
r _T	T _j = 150 °C		20		mΩ
R _{th(j-s)}	per diode		1,5		K/W
Temperature Sensor					
R _{ts}	3 %, T _r = 25 (100) °C		1000(1670)		Ω
Mechanical Data					
w			35		g
M _s	Mounting torque	2		2,5	Nm







This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our personal.